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44. The method of claim 41, wherein:  
the step of applying a first voltage includes applying the first voltage to a control gate terminal of the memory cell; and  
the step of applying a second voltage includes applying the second voltage to the control gate terminal of the memory cell.--


#### REMARKS

The new claims have been copied from patent no. 5,652,720 - Aulas et al. (1997), a copy of which is being filed herewith. New claims 35-44 correspond, respectively, to claims 37, 38, 40-43, 20, 23, 26 and 27 of the Aulas et al. patent. All are exact copies except for dependent claims 38 and 39 which are modified versions of the patent claims 41 and 42.

A prompt examination and allowance of this application are solicited.

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Respectfully submitted,

  
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